

Weak Antilocalization in Polycrystalline SnTe Films Deposited by Magnetron Sputtering

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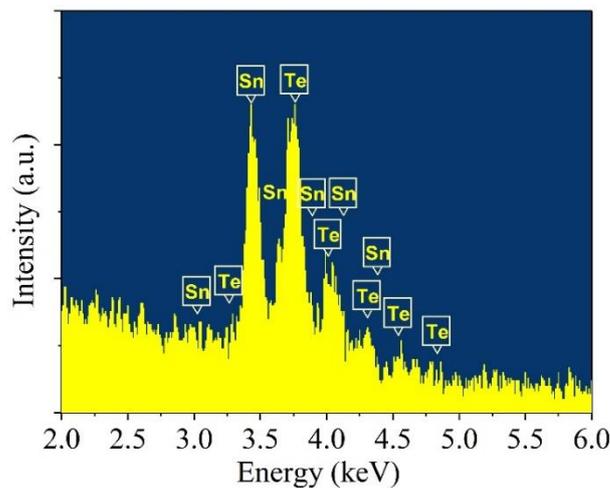


Figure S1. Energy dispersive X-ray spectrum of the as-deposited SnTe film. The atomic ratio of Sn:Te is measured to be 51.6: 48.4.

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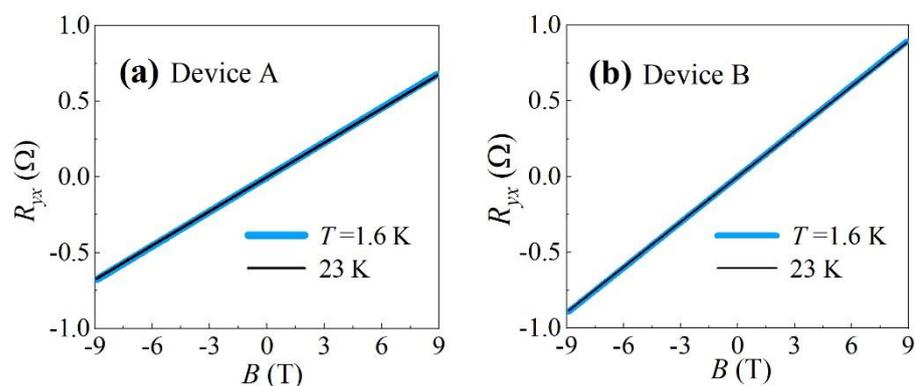


Figure S2. (a) Hall resistance of device A, measured at $T = 1.6\text{K}$ and 23K . (b) Hall resistance of device B, measured at $T = 1.6\text{K}$ and 23K .

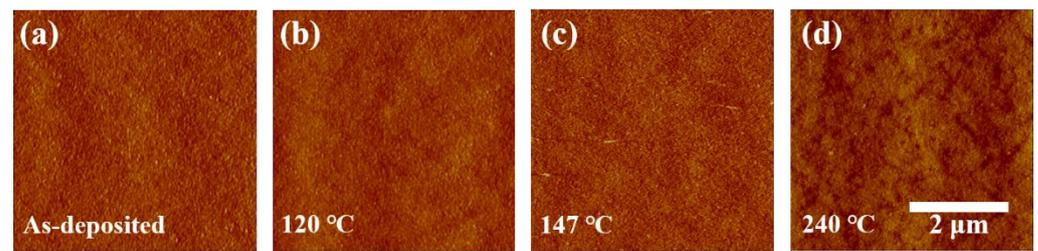


Figure S3. (a-d) AFM images of SnTe films annealed at various temperatures. The scanning area is $5 \times 5 \mu\text{m}^2$.